	Application No.	Applicant(s)	
Notice of Allowability	10/750,084	LIM ET AL.	$\langle \omega \rangle$
	Examiner	Art Unit	<u> </u>
	Trung Dang	2823	
	Trung Dang	2023	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
1. This communication is responsive to the telephone interview on 11/15/05.			
2. \(\sum \) The allowed claim(s) is/are 2.3 and 5-19.			
3. ☑ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) ☑ All b) ☐ Some* c) ☐ None of the:			
1. Certified copies of the priority documents have been received.			
2. Certified copies of the priority documents have been received in Application No			
3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
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Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.			
4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.			
5. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.			
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached			
1) 🔲 hereto or 2) 🔲 to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date			
Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).			
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.			
Attachment(s)	5 District of Information	Data at Analisation (DTO)	450)
1. Notice of References Cited (PTO-892)	5. Notice of Informal F		152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary Paper No./Mail Da	ite	
 Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 		ment/Comment	
Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. Examiner's Stateme	ent of Reasons for Allowa	ance
or blological iviaterial	9. 🗌 Other		

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EXAMINER'S AMENDMENT

1. An extension of time under 37 CFR 1.136(a) is required in order to make an examiner's amendment which places this application in condition for allowance. During a telephone conversation with Steven Y. Cho conducted on, 11/15/05 requested an extension of time for one MONTH(S) and authorized the Director to charge Deposit Account No. 20-1430 the required fee of \$110.00 for this extension and authorized the following examiner's amendment. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

- **Claim 2**, delete ", wherein the dielectric capping layer a silicon oxide-based layer".

- Replace amended claim 5 as follows:

A method for fabricating a transistor with a polymetal gate electrode structure, the method comprising:

forming a gate insulation layer on a substrate;

forming a patterned gate stack structure over the gate insulation layer, wherein the patterned stack structure includes a polysilicon layer as a lower layer and a metal layer as an upper layer;

forming a silicon oxide-based capping layer along a profile containing the patterned gate stack structure and on the gate insulation layer at a predetermined temperature that prevents oxidation of the metal layer, the silicon oxide-based capping layer including a horizontal portion and a vertical portion that together enclose the patterned gate stack structure; and

performing a gate re-oxidation process,

wherein the silicon oxide-based capping laver is formed by performing an atomic layer deposition (ALD) technique which includes the steps of:

loading a wafer containing the patterned gate stack structure into a chamber;

flowing a source gas of silicon (Si) into the chamber and purging the remaining gas; and

flowing a source gas of oxygen into the chamber and purging the remaining gas.

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Trung Dang whose telephone number is 571-272-1857. The examiner can normally be reached on Mon-Friday 9:30am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Trung Dang
Primary Examiner
Art Unit 2823

11/15/05